NSN 5961-01-177-4018

Semiconductor Device Set - Page 1 of 2

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Inclosure Material:

Metal all transistor

Overall Length:

1.062 inches all transistor and 1.245 inches all transistor

Mounting Facility Quantity:

1 all transistor

Internal Configuration:

Junction contact all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

4 transistor

Mounting Method:

Threaded stud all transistor

Features Provided:

Burn in

Overall Width Across Flats:

0.667 inches all transistor and 0.687 inches all transistor

Thread Size:

0.250 inches all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

400.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter all transistor and 350.0 breakdown voltage, collector-to-emitter, base open all transistor and 20.0 breakdown voltage, emitter-to-base, collector open all transistor

Current Rating Per Characteristic:

10.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

75.0 watts small-signal input power, common-collector preset all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction all transistor

Thread Series Designator:

Unf all transistor

Terminal Type And Quantity:

3 tab, solder lug all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A110a0